

GaAs LPE Epitaxial Wafers

Feature

- Good uniformity(power, Epi-Thickness, Total Thickness).
- Mirror like surface.
- High reliability.
- Stability of p-n interface without thyristor.

Application

Infrared LED

- Coupler, Interrupter
- Remote Controller

Standard Specifications

Application		IR-LED		Higher Output IR-LED	
Product Name		GS-960-70	GS-960-45	GW-95	GL-880-SI
Wavelength(mm)		955±15	950±15	940±15	880±10
Structure		② P-GaAs(Si) ① n-GaAs(Si) n-GaAs(Si)Sub.		③ P-AlGaAs(Zn) ② P-GaAs(Si) ① n-GaAs(Si) n-GaAs(Si)Sub. ① n-AlGaAs(Si) ② p-AlGaAs(Si)	
Epi.	③ C.C.(cm ⁻³) Thickness(μm)	—	—	≥0.8×10 ¹⁸ 25 ~ 75	—
	② C.C.(cm ⁻³) Thickness(μm)	≥5×10 ¹⁸ 55 ~ 95	≥1×10 ¹⁸ 25 ~ 65	— 5 ~ 40	≥1×10 ¹⁸ 140 ~ 220
	① C.C.(cm ⁻³) Thickness(μm)	— 30 ~ 70	— 25 ~ 65	— 25 ~ 65	≥1×10 ¹⁷ 30 ~ 110
Sub.	Size	Within 64mmφ, 78mmφ			Within 64mmφ
	C.C.(cm ⁻³)	≥0.5×10 ¹⁷			Removed
	Orientation	(100)±0.5°			
	Type	N			
Total Thickness		200 ~ 350			

Other Specifications are available on request.